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ON Semiconductor®

# FQP27P06

## P-Channel QFET<sup>®</sup> MOSFET

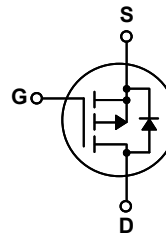
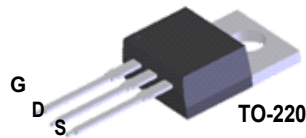
- 60 V, - 27 A, 70 mΩ

### Description

This P-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### Features

- - 27 A, - 60 V,  $R_{DS(on)} = 70 \text{ m}\Omega$  (Max.) @  $V_{GS} = - 10 \text{ V}$ ,  $I_D = - 13.5 \text{ A}$
- Low Gate Charge (Typ. 33 nC)
- Low  $C_{rss}$  (Typ. 120 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQP27P06	Unit
$V_{DSS}$	Drain-Source Voltage	-60	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	-27
		- Continuous ( $T_C = 100^\circ\text{C}$ )	-19.1
$I_{DM}$	Drain Current - Pulsed (Note 1)	-108	A
$V_{GSS}$	Gate-Source Voltage	$\pm 25$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	560	mJ
$I_{AR}$	Avalanche Current (Note 1)	-27	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	12	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-7.0	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ )	120	W
		- Derate above $25^\circ\text{C}$	0.8
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	FQP27P06	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.25	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	$^\circ\text{C}/\text{W}$

FQP27P06 P-Channel QFET<sup>®</sup> MOSFET

## Electrical Characteristics

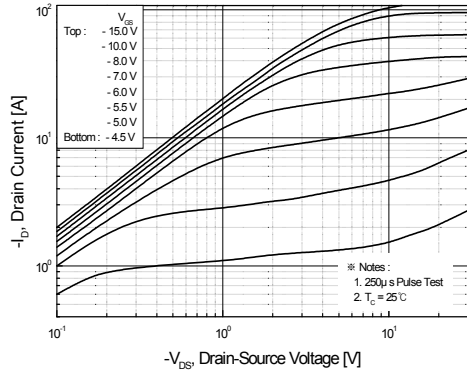
$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-60	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	-0.06	--	V/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$	--	--	-1	$\mu\text{A}$
		$V_{DS} = -48\text{ V}, T_C = 150^\circ\text{C}$	--	--	-10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-2.0	--	-4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -13.5\text{ A}$	--	0.055	0.07	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = -30\text{ V}, I_D = -13.5\text{ A}$	--	12.4	--	S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1100	1400	pF
$C_{oss}$	Output Capacitance		--	510	660	pF
$C_{rss}$	Reverse Transfer Capacitance		--	120	155	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -30\text{ V}, I_D = -13.5\text{ A},$ $R_G = 25\ \Omega$	--	18	45	ns
$t_r$	Turn-On Rise Time		--	185	380	ns
$t_{d(off)}$	Turn-Off Delay Time		--	30	70	ns
$t_f$	Turn-Off Fall Time		(Note 4)	--	90	190
$Q_g$	Total Gate Charge	$V_{DS} = -48\text{ V}, I_D = -27\text{ A},$ $V_{GS} = -10\text{ V}$	--	33	43	nC
$Q_{gs}$	Gate-Source Charge		--	6.8	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4)	--	18	--
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current		--	--	-27	A
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current		--	--	-108	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -27\text{ A}$	--	--	-4.0	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = -27\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	105	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	0.41	--	$\mu\text{C}$

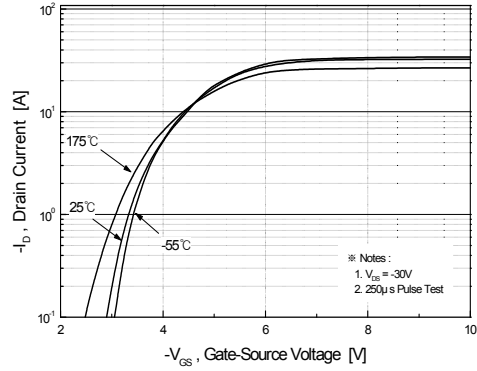
**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 0.9\text{ mH}, I_{AS} = -27\text{ A}, V_{DD} = -25\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq -27\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature

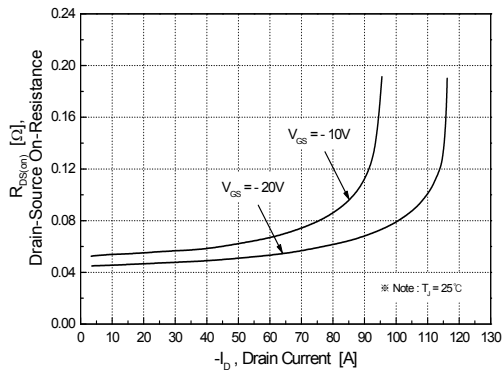
## Typical Characteristics



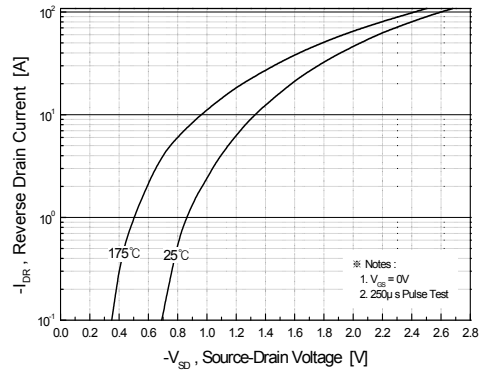
**Figure 1. On-Region Characteristics**



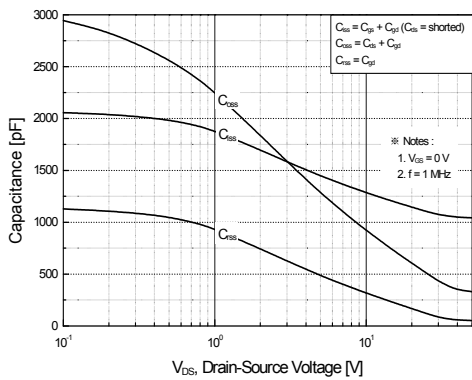
**Figure 2. Transfer Characteristics**



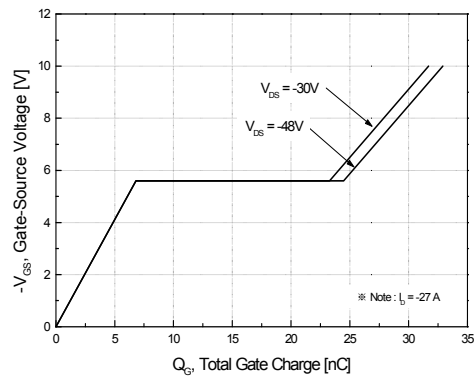
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**

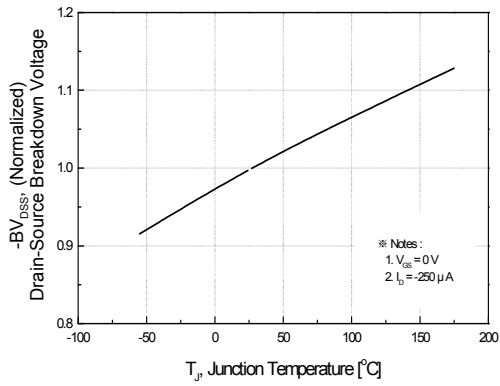


**Figure 5. Capacitance Characteristics**

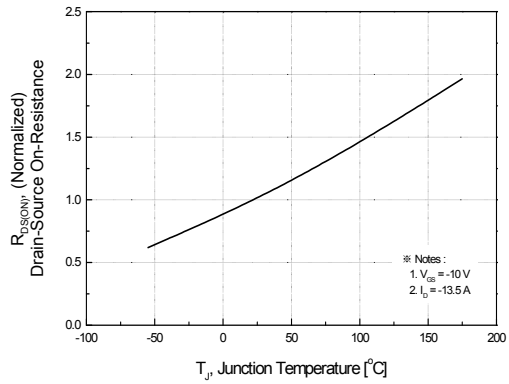


**Figure 6. Gate Charge Characteristics**

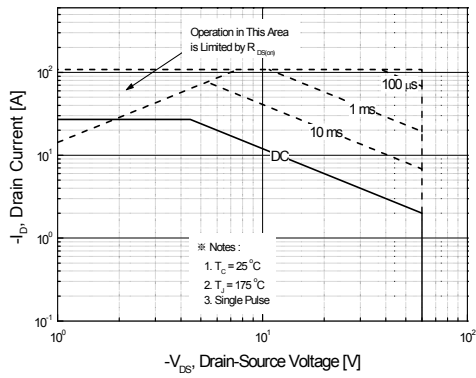
**Typical Characteristics** (Continued)



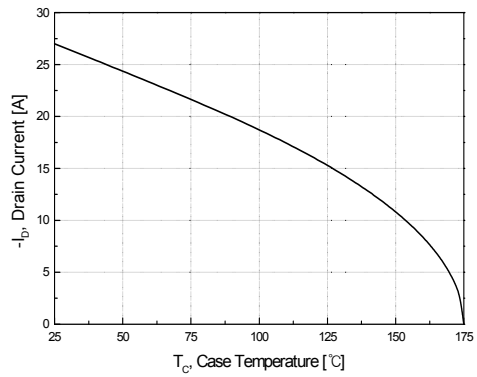
**Figure 7. Breakdown Voltage Variation vs. Temperature**



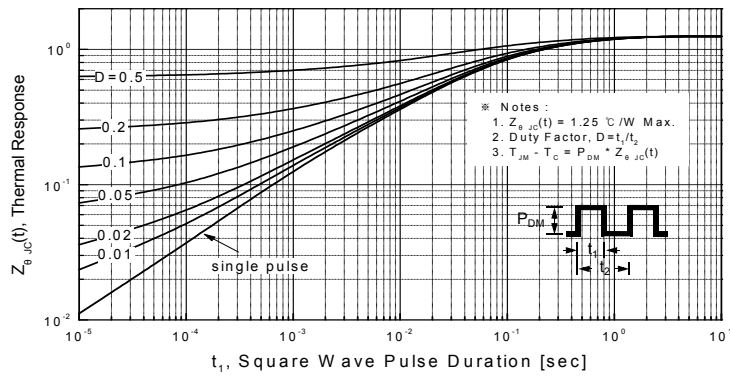
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**

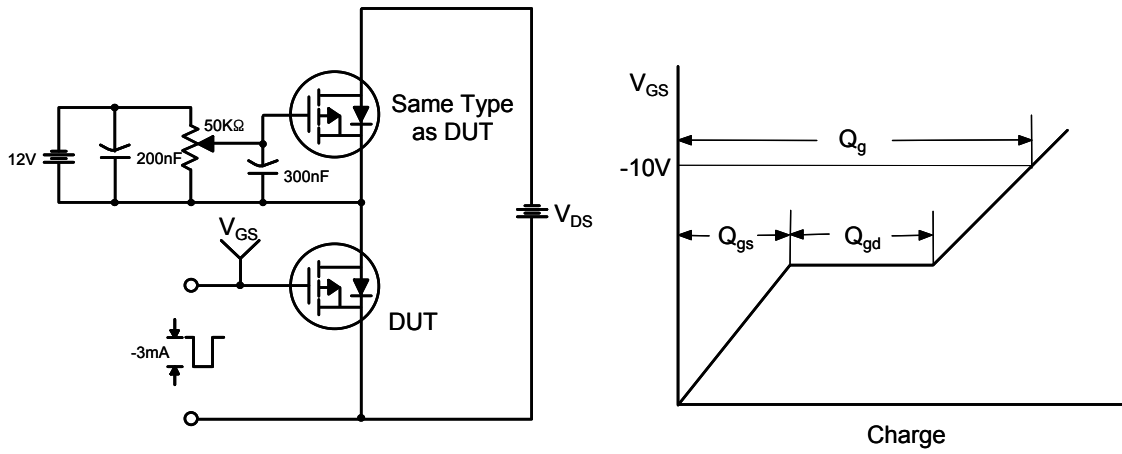


**Figure 10. Maximum Drain Current vs. Case Temperature**

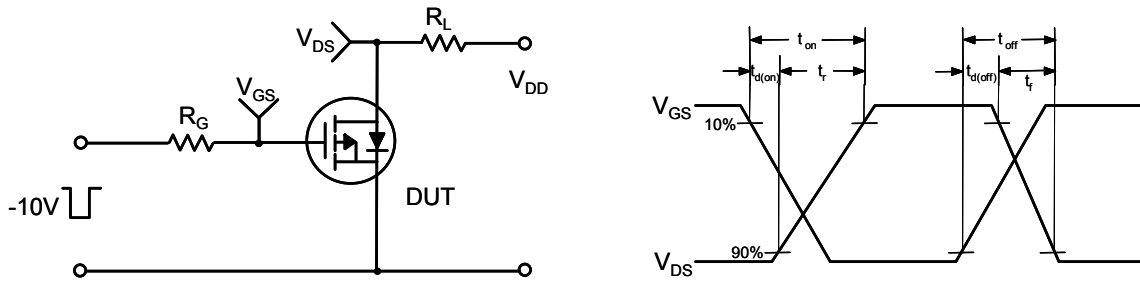


**Figure 11. Transient Thermal Response Curve**

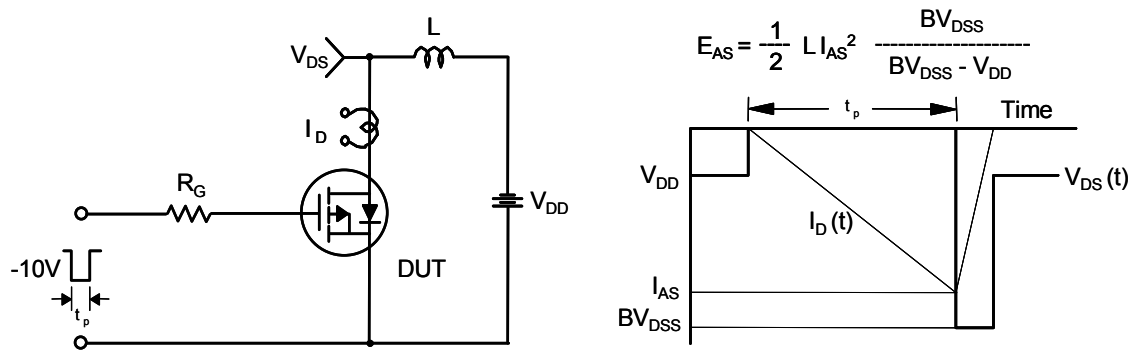
**Gate Charge Test Circuit & Waveform**



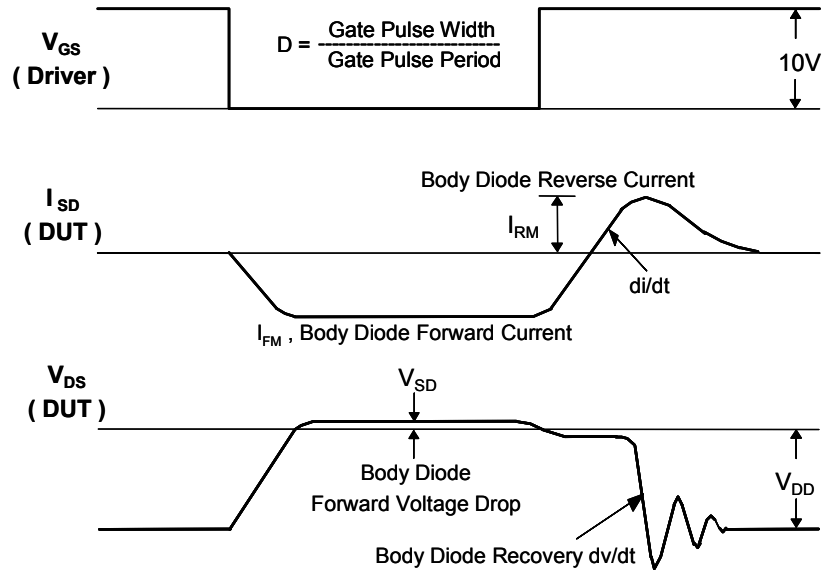
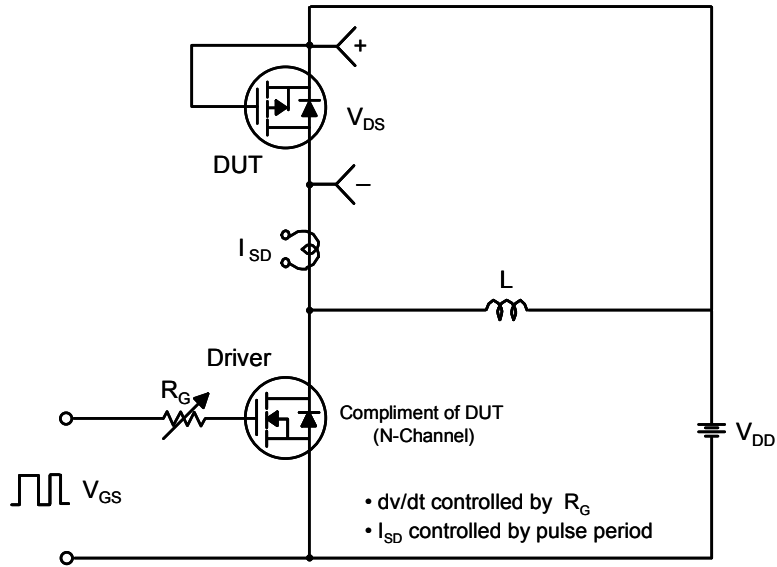
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

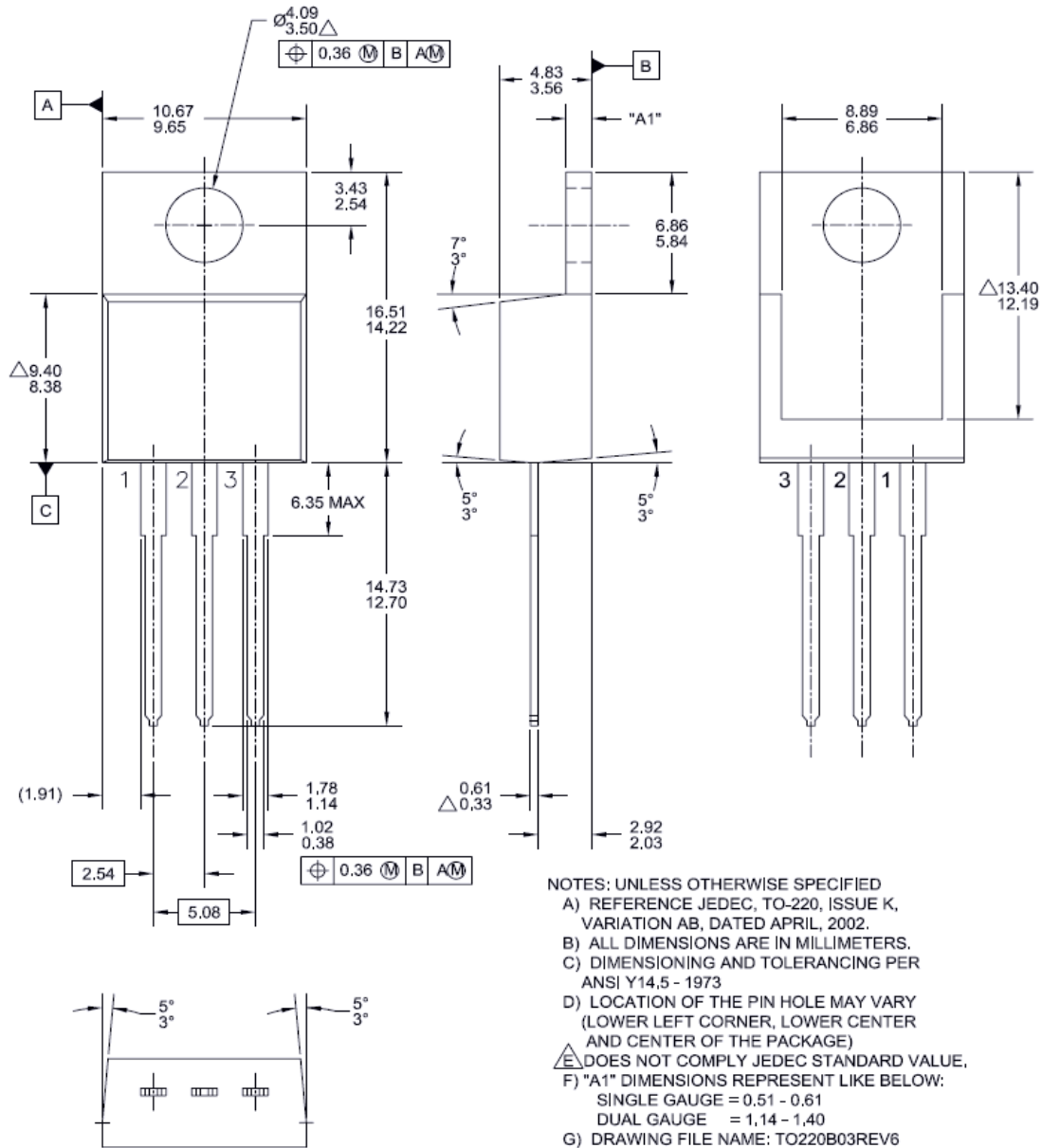


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

TO-220



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) REFERENCE JEDEC, TO-220, ISSUE K, VARIATION AB, DATED APRIL, 2002.
  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5 - 1973
  - D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
  - E)  $\Delta$  DOES NOT COMPLY JEDEC STANDARD VALUE.
  - F) "A1" DIMENSIONS REPRESENT LIKE BELOW:  
SINGLE GAUGE = 0.51 - 0.61  
DUAL GAUGE = 1.14 - 1.40
  - G) DRAWING FILE NAME: TO220B03REV6

FQP27P06 P-Channel QFET<sup>®</sup> MOSFET



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